

1. Scope :

This specification applies to P/N silicon TVS diode chips,
Device NO. SD-12908

2. Structure :

- 2-1. Planar type : P/N Diode.
- 2-2. Electrodes :
Top side : Aluminum alloy.
Back side : Gold layer.

3. Size :

- 3-1. Chip size : 31.5 mils x 27.6 mils (0.800 mm x 0.700 mm).
- 3-2. Chip thickness : 5.9 ± 1.0 mils (0.150 ± 0.0254 mm)
- 3-3. Bonding pad : 26.8 mils x 22.8 mils (0.680 mm x 0.580 mm).
- 3-4. Pattern drawing : Refer to the attached drawing.

4. Electrical characteristics (Ta = 25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse Current	I_R	$V_R=5V$ $E_e=0mW/cm^2$			2000	nA
Reverse Breakdown Voltage	$V_{(BR)}$	$I_R=5mA$ $E_e=0mW/cm^2$	7		9	V
Forward Voltage	V_f	$I_F=10mA$ $E_e=0mW/cm^2$			1.2	V

